

μESD3.3DT5G SERIES

ESD Protection Diodes

Ultra Small SOT-723 Package

The μESD Series is designed to protect voltage sensitive components from ESD. Excellent clamping capability, low leakage, and fast response time, make these parts ideal for ESD protection on designs where board space is at a premium. Because of its small size, it is suited for use in cellular phones, portable devices, digital cameras, power supplies and many other portable applications.

Specification Features:

- Small Body Outline Dimensions:
0.047" x 0.032" (1.20 mm x 0.80 mm)
- Low Body Height: 0.020" (0.5 mm)
- Stand-off Voltage: 3.3 V – 6.0 V
- Low Leakage
- Response Time is Typically < 1 ns
- ESD Rating of Class 3 (> 16 kV) per Human Body Model
- IEC61000-4-2 Level 4 ESD Protection
- IEC61000-4-4 Level 4 EFT Protection
- AEC-Q101 Qualified and PPAP Capable
- These are Pb-Free Devices

Mechanical Characteristics:

CASE: Void-free, transfer-molded, thermosetting plastic
Epoxy Meets UL 94 V-0

LEAD FINISH: 100% Matte Sn (Tin)

MOUNTING POSITION: Any

QUALIFIED MAX REFLOW TEMPERATURE: 260°C

Device Meets MSL 1 Requirements

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
IEC 61000-4-2 (ESD) Air Contact		±30 ±30	kV
IEC 61000-4-4 (EFT)		40	A
ESD Voltage Per Human Body Model Per Machine Model		16 400	kV V
Total Power Dissipation on FR-5 Board (Note 1) @ T _A = 25°C Derate above 25°C	P _D	240 1.9	mW mW/°C
Thermal Resistance Junction-to-Ambient	R _{θJA}	525	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C
Lead Solder Temperature – Maximum (10 Second Duration)	T _L	260	°C

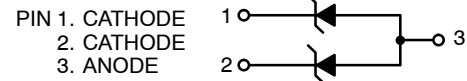
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-5 = 1.0 x 0.75 x 0.62 in.



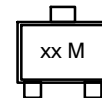
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SOT-723
CASE 631AA
STYLE 4

MARKING DIAGRAM



xx = Device Code
M = Date Code

ORDERING INFORMATION

Device	Package	Shipping†
UESDxxDT5G	SOT-723	8000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

DEVICE MARKING INFORMATION

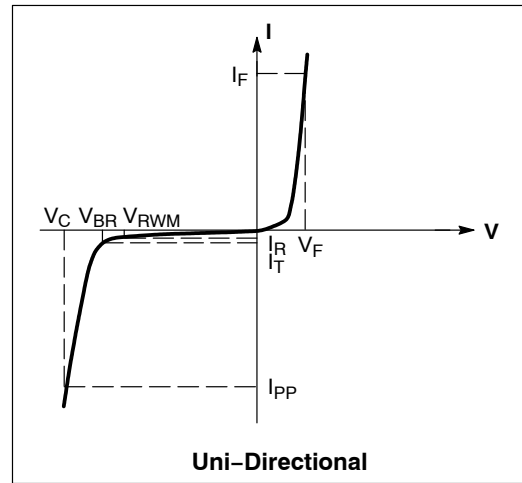
See specific marking information in the device marking column of the table on page 2 of this data sheet.

μESD3.3DT5G SERIES

ELECTRICAL CHARACTERISTICS

($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
I_F	Forward Current
V_F	Forward Voltage @ I_F
P_{pk}	Peak Power Dissipation
C	Max. Capacitance @ $V_R = 0$ and $f = 1$ MHz



ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted, $V_F = 1.1$ V Max. @ $I_F = 10$ mA for all types)

Device*	Device Marking	V_{RWM} (V)	I_R (μA) @ V_{RWM}	V_{BR} (V) @ I_T (Note 2)	I_T	C (pF)
		Max	Max	Min	mA	Typ
UESD3.3DT5G	L0	3.3	1.0	5.0	1.0	47
UESD5.0DT5G	L2	5.0	0.1	6.2	1.0	38
UESD6.0DT5G	L3	6.0	0.1	7.0	1.0	34

*Other voltages available upon request.

2. V_{BR} is measured with a pulse test current I_T at an ambient temperature of 25°C .

μESD3.3DT5G SERIES

TYPICAL CHARACTERISTICS

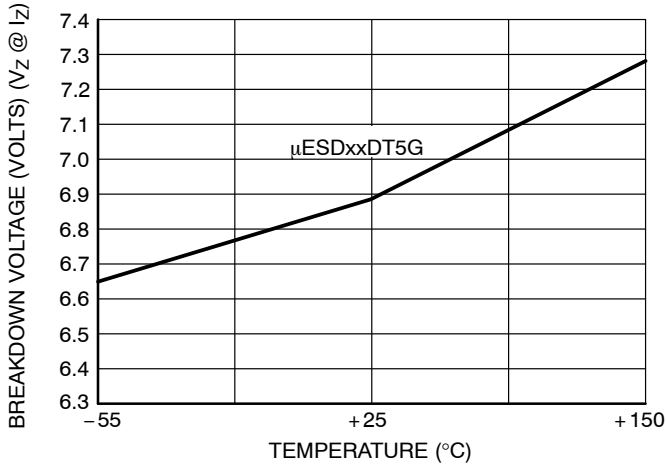


Figure 1. Typical Breakdown Voltage versus Temperature

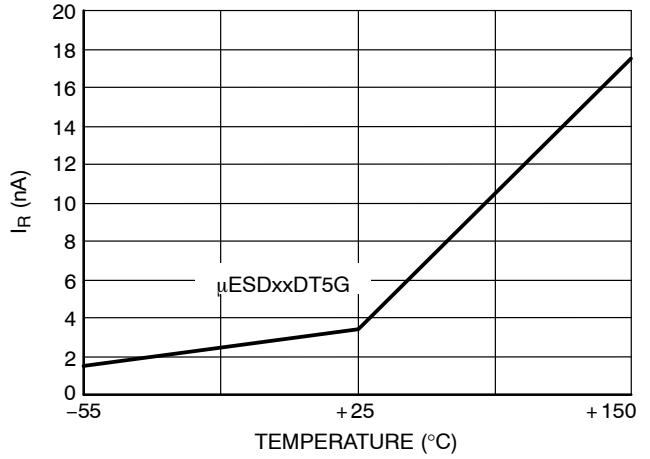


Figure 2. Typical Leakage Current versus Temperature

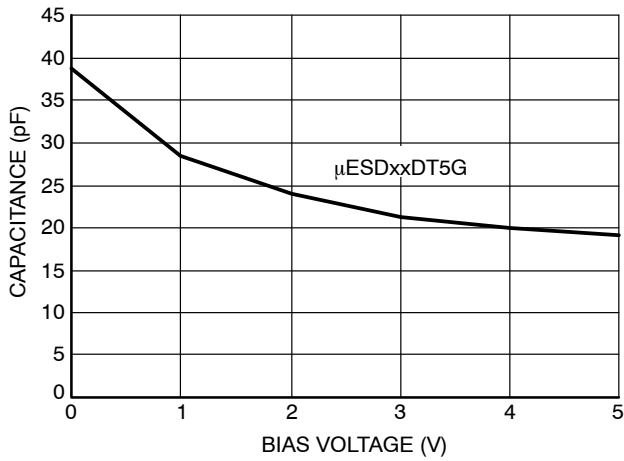


Figure 3. Typical Capacitance versus Bias Voltage

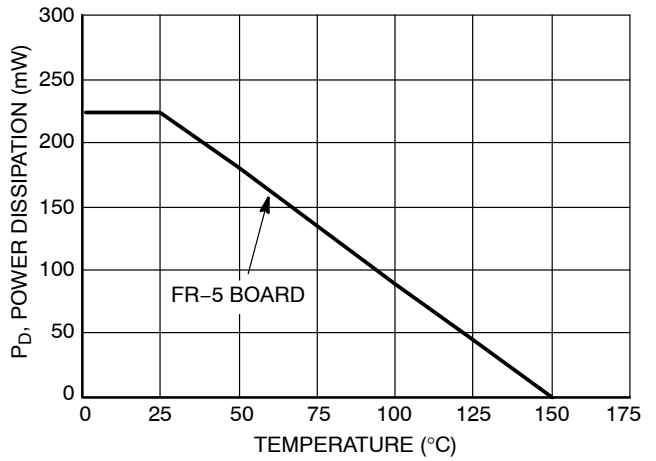


Figure 4. Steady State Power Derating Curve

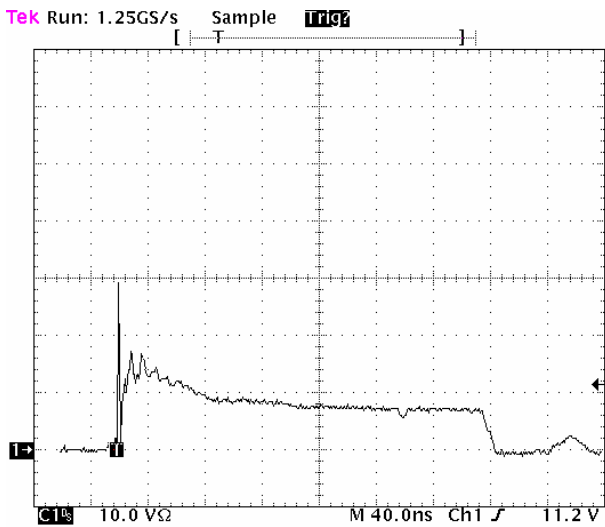


Figure 5. Positive 8 kV contact per IEC 6100-4-2
- μESD5.0DT5G

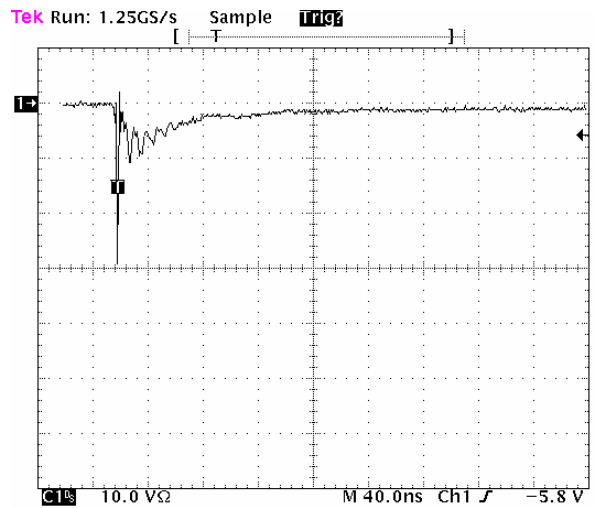
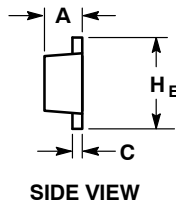
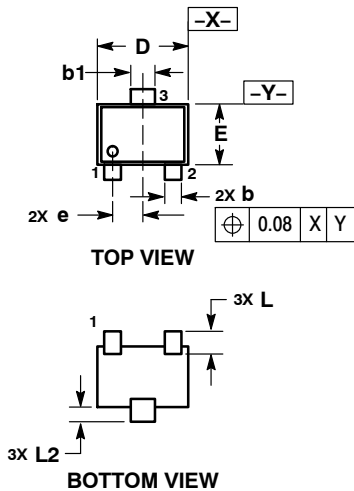


Figure 6. Negative 8 kV contact per IEC 6100-4-2
- μESD5.0DT5G

μESD3.3DT5G SERIES

PACKAGE DIMENSIONS

SOT-723
CASE 631AA
ISSUE D



NOTES:

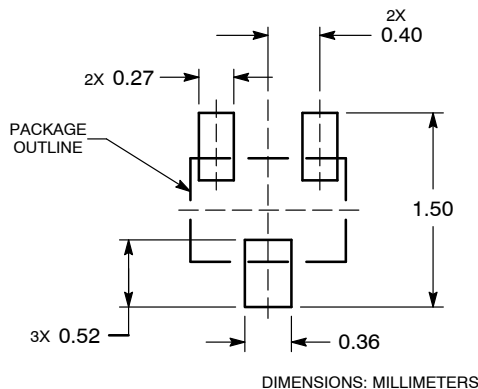
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.45	0.50	0.55
b	0.15	0.21	0.27
b1	0.25	0.31	0.37
C	0.07	0.12	0.17
D	1.15	1.20	1.25
E	0.75	0.80	0.85
e	0.40 BSC		
H E	1.15	1.20	1.25
L	0.29 REF		
L2	0.15	0.20	0.25

STYLE 4:

1. CATHODE
2. CATHODE
3. ANODE

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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